



**MMBT3906FZ** 

#### 40V PNP SMALL SIGNAL TRANSISTOR IN DFN0606

### Features

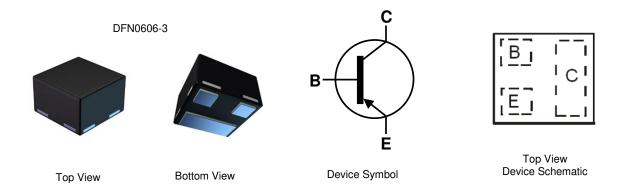
- BV<sub>CEO</sub> > -40V
- I<sub>C</sub> = -200mA High Collector Current
- P<sub>D</sub> = 925mW Power Dissipation
- 0.36mm<sup>2</sup> Package Footprint, 40% Smaller than DFN1006
- 0.4mm Height Package Minimizing Off-Board Profile
- Complementary NPN Type MMBT3904FZ
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

## **Mechanical Data**

- Case: X2-DFN0606-3
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020

3N = Product Type Marking Code

- Terminals: Finish NiPdAu, Solderable per MIL-STD-202, Method 208 (24)
- Weight: 0.0008 grams (Approximate)



## Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMBT3906FZ-7B	3N	7	8	10,000

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

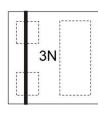
2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**

Notes:



Top View Bar Denotes Base and Emitter Side

MMBT3906FZ Document number: DS37159 Rev. 1 - 2



#### Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-40	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-40	V
Emitter-Base Voltage	V <sub>EBO</sub>	-6.0	V
Collector Current	Ic	-200	mA
Peak Pulse Collector Current	I <sub>CM</sub>	-500	mA

#### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	Р	270	- mW	
Power Dissipation	(Note 6)	P <sub>D</sub>	925		
Thermal Desistance, Junction to Ambient	(Note 5)	P	465	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	R <sub>0JA</sub>	135	°C/W	
Thermal Resistance, Junction to Lead (Note 7)		R <sub>θJL</sub>	135	°C/W	
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C		

## ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	200	V	В

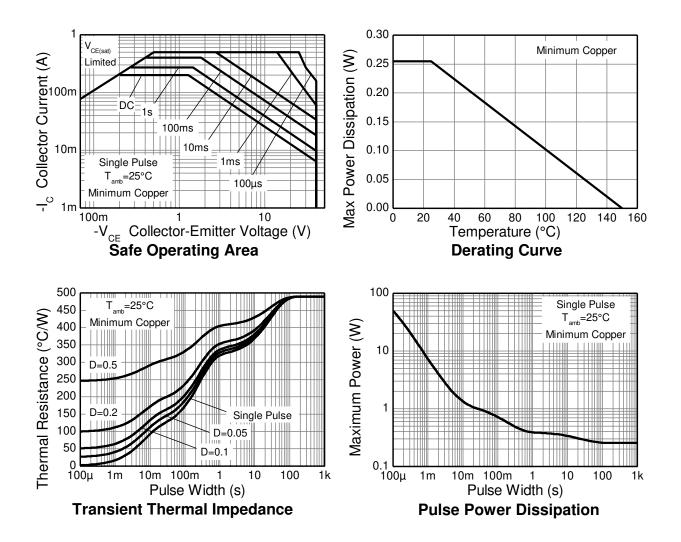
 For the device mounted on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady state condition. The entire exposed collector pad is attached to the heatsink.
 Same as Note 5, except the exposed collector pad is mounted on 25mm x 25mm 2oz copper. Notes:

7. Thermal resistance from junction to solder-point (on the exposed collector pad).

8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



# **Thermal Characteristics and Derating Information**





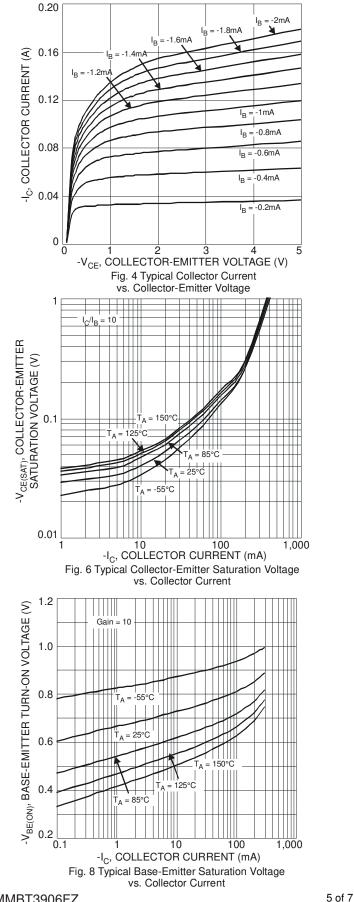
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

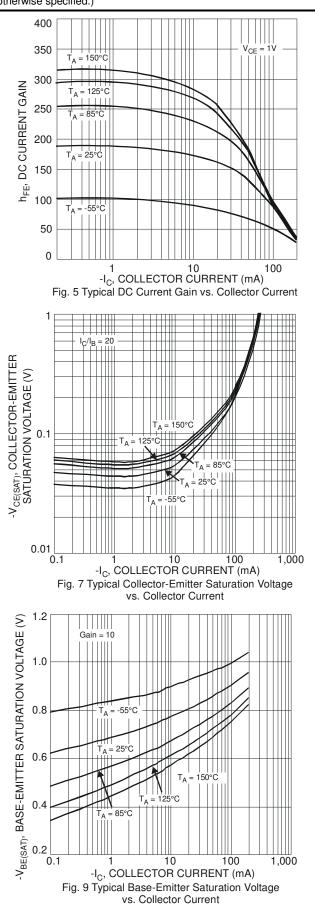
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-40	—	V	$I_{\rm C} = -100 \mu A, \ I_{\rm E} = 0$
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	-40	—	V	$I_{\rm C} = -10.0 {\rm mA}, I_{\rm B} = 0$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-6.0	—	V	$I_{E} = -100 \mu A, I_{C} = 0$
Collector Cutoff Current	ICEX	—	-50	nA	$V_{CE} = -30V, V_{EB(OFF)} = -3.0V$
Collector Cutoff Current	I <sub>CBO</sub>	—	-50	nA	$V_{CB} = -30V, I_E = 0$
Base Cutoff Current	I <sub>BL</sub>	—	-50	nA	$V_{CE} = -30V, V_{EB(OFF)} = -3.0V$
ON CHARACTERISTICS (Note 9)					
DC Current Gain	h <sub>FE</sub>	60 80 100 60 30	 300 	_	$\begin{split} I_{C} &= -100\mu A, \ V_{CE} &= -1.0V \\ I_{C} &= -1.0mA, \ V_{CE} &= -1.0V \\ I_{C} &= -10mA, \ V_{CE} &= -1.0V \\ I_{C} &= -50mA, \ V_{CE} &= -1.0V \\ I_{C} &= -100mA, \ V_{CE} &= -1.0V \end{split}$
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	—	-0.25 -0.40	V	$I_{C} = -10mA$ , $I_{B} = -1.0mA$ $I_{C} = -50mA$ , $I_{B} = -5.0mA$
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	-0.65	-0.85 -0.95	V	$I_{C} = -10mA, I_{B} = -1.0mA$ $I_{C} = -50mA, I_{B} = -5.0mA$
SMALL SIGNAL CHARACTERISTICS	•	•		•	
Output Capacitance	Cobo	—	4.5	pF	$V_{CB} = -5.0V$ , f = 1.0MHz, I <sub>E</sub> = 0
Input Capacitance	C <sub>ibo</sub>	—	10	pF	V <sub>EB</sub> = -0.5V, f = 1.0MHz, I <sub>C</sub> = 0
Current Gain-Bandwidth Product	f <sub>T</sub>	300	_	MHz	$V_{CE} = -20V, I_C = -10mA, f = 100MHz$
SWITCHING CHARACTERISTICS					
Delay Time	t <sub>d</sub>	—	35	ns	$V_{CC} = -3.0V, I_{C} = -10mA,$
Rise Time	tr	—	35	ns	$V_{BE(off)} = 0.5V, \ I_{B1} = -1.0mA$
Storage Time	ts	_	225	ns	$V_{CC} = -3.0V, I_{C} = -10mA,$
Fall Time	t <sub>f</sub>	_	75	ns	$I_{B1} = I_{B2} = -1.0 \text{mA}$

Note: 9. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2%.



### **Typical Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

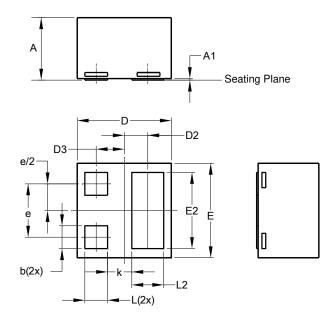






# **Package Outline Dimensions**

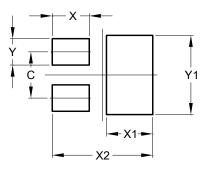
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	X2-DFN0606-3				
Dim	Min	Max	Тур		
Α	0.36	0.42	0.39		
A1	0	0.05	0.02		
b	0.10	0.20	0.15		
D	0.57 0.67 0.62				
D2	0.155 BSC				
D3	0.185 BSC				
E	0.57 0.67 0		0.62		
E2	0.40	0.60	0.50		
е	0.35 BSC				
k	0.16 REF				
L	0.09	0.21	0.15		
L2	0.11	0.31	0.21		
All	All Dimensions in mm				

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)	
С	0.350	
Х	0.280	
X1	0.350	
X2	0.760	
Y	0.200	
Y1	0.600	



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